

AMENDMENTS TO THE SPECIFICATION

Please replace the paragraph beginning on page 4, line 21 with the following amended paragraph:

Since the disclosed acidic slurry for oxide films has a lower polishing selectivity ratio to polysilicon layers than that of the oxide films, the disclosed acidic slurry also comprises an oxidizer to improve a the polishing selectivity ratio to polyerystalline substances the polysilicon layer.

Please replace the paragraph beginning on page 5, line 4 with the following amended paragraph:

It is preferable that the hard mask film ~~composes of~~ comprises nitride film, and ~~the wordline conductive layer composes a SiON or organic bottom ARC layer.~~